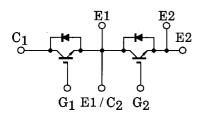
TOSHIBA GTR Module Silicon N Channel IGBT

# MG120V2YS40

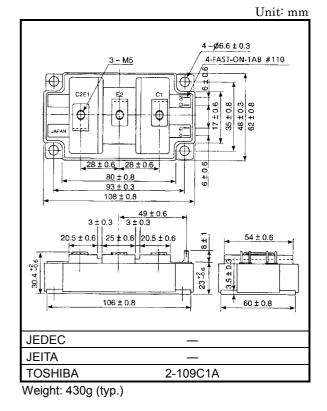
High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High speed :  $t_f = 1.5 \mu s (max) (I_C = 120A)$  $t_{rr} = 0.6 \mu s (max) (I_F = 120A)$

### **Equivalent Circuit**



### Maximum Ratings (Ta = 25°C)

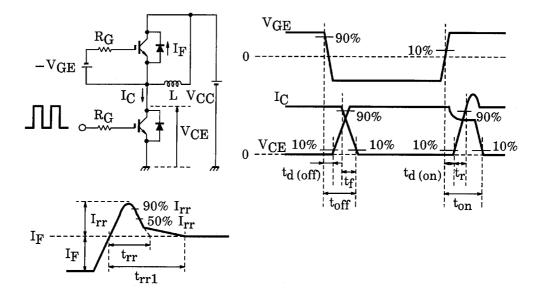


Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	1700	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ι <sub>C</sub>	120	A	
	1ms	I <sub>CP</sub>	240		
Forward current	DC	١ <sub>F</sub>	120	A	
	1ms	I <sub>FM</sub>	240		
Collector power dissipation (Tc = 25°C)		PC	1200	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	4000 (AC 1 min.)	V	
Screw torque (Terminal / mounting)			3/3	N∙m	

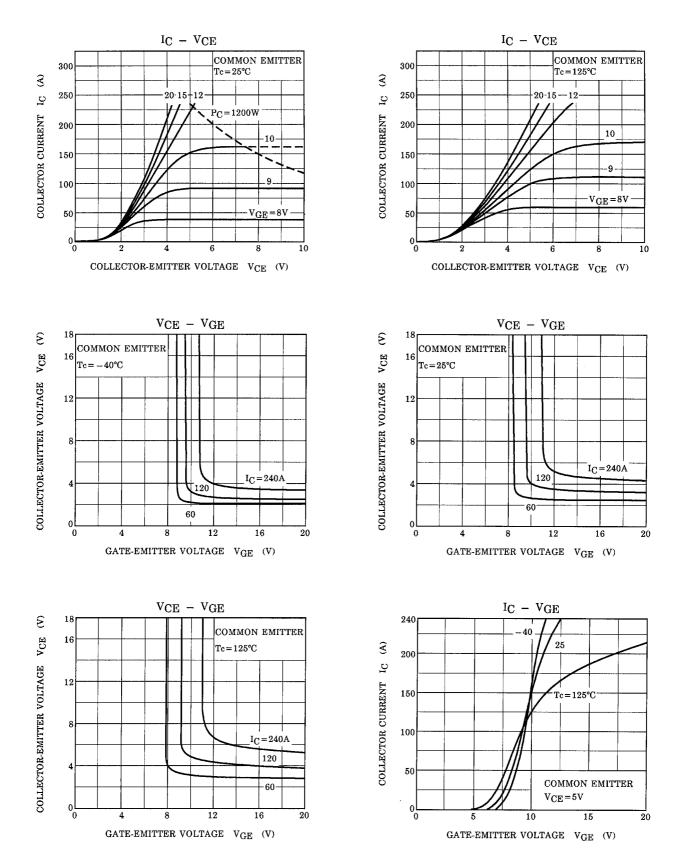
**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20V, V_{CE} = 0$	_	—	±100	nA
Collector cut-off current		ICES	V <sub>CE</sub> = 1700V, V <sub>GE</sub> = 0	_	_	1	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 120mA, V <sub>CE</sub> = 5V	4.0	-	8.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 120A, V <sub>GE</sub> = 15V	_	3.2	4.5	V
Input capacitance		Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	_	16400	_	pF
Switching time	Turn-on delay time	t <sub>d(on)</sub>	Inductive load $V_{CC} = 900V$ $I_C = 120A$ $V_{GE} = \pm 15V$ $R_G = 4.7\Omega$ (Note 1)	_	0.1	_	μs
	Rise time	t <sub>r</sub>		_	0.1	_	
	Turn-on time	t <sub>on</sub>		_	0.5	_	
	Turn-off delay time	t <sub>d(off)</sub>		_	0.4	_	
	Fall time	t <sub>f</sub>		_	0.5	1.5	
	Turn-off time	t <sub>off</sub>		_	1.0	_	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 120A, V <sub>GE</sub> = 0	_	3.5	4.5	V
Reverse recovery time		t <sub>rr</sub>	I <sub>F</sub> = 120A, V <sub>GE</sub> = -15V di / dt = 500A / μs (Note 1)	_	0.3	0.6	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage	_	_	0.104	°C/W
			Diode stage	_	-	0.25	

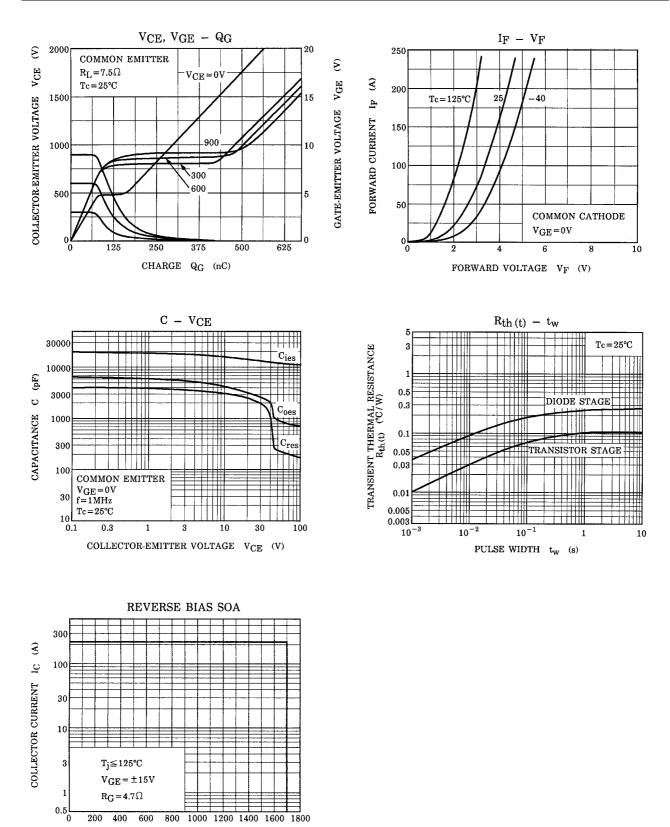
Note 1: Switching time and reverse recovery time test circuit & timing chart



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COLLECTOR-EMITTER VOLTAGE VCE (V)

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